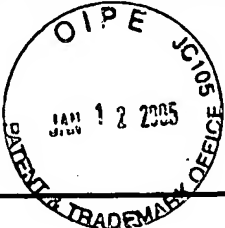


FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT				ATTORNEY DOCKET NO.: ASC-025DVC1 APPLICANTS: Cheng <i>et al.</i> SERIAL NO.: 10/802,185 FILING DATE: March 17, 2004 GROUP: 2813					
									
U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
CAT	B48	6-244112	09/02/1994	JP				Y	Y
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
CAT	C102	Batterman, "Hillocks, Pits, and Etch Rate in Germanium Crystals," <u>Journal of Applied Physics</u> , Vol. 28, No. 11 (November, 1957), pp. 1236-1241.							
CAT	C103	Bohg, "Ethylene Diamine-Pyrocatechol-Water Mixture Shows Etching Anomaly in Boron-Doped Silicon," <u>Journal of the Electrochemical Society</u> , Vol. 118, No. 2 (February 1971), pp. 401-402.							
CAT	C104	Brunner et al., "Molecular beam epitaxy growth and thermal stability of Si _{1-x} Ge _x layers on extremely thin silicon-on-insulator substrates," <u>Thin Solid Films</u> , Vol. 321 (1998), pp. 245-250.							
CAT	C105	Chen et al., "The Band Model and the Etching Mechanism of Silicon in Aqueous KOH," <u>Journal of the Electrochemical Society</u> , Vol. 142, No. 1 (January 1995), pp. 170-176.							
CAT	C106	Desmond <i>et al.</i> , "The Effects of Process-Induced Defects on the Chemical Selectivity of Highly Doped Boron Etch Stops in Silicon," <u>Journal of the Electrochemical Society</u> , Vol. 141, No. 1 (January 1994), pp. 178-184.							
CAT	C107	Ehman <i>et al.</i> , "Morphology of Etch Pits on Germanium Studied by Optical and Scanning Electron Microscopy," <u>Journal of Applied Physics</u> , Vol. 41, No. 7 (June 1970), pp. 2824-2827.							
CAT	C108	Feijóo <i>et al.</i> , "Etch Stop Barriers in Silicon Produced by Ion Implantation of Electrically Non-Active Species," <u>Journal of the Electrochemical Society</u> , Vol. 139, No. 8 (August 1992), pp. 2309-2313.							
CAT	C109	Finne et al., "A Water-Amine-Complexing Agent System for Etching Silicon," <u>Journal of the Electrochemical Society</u> , Vol. 114, No. 9 (September 1967), pp. 965-970.							
CAT	C110	Fitzgerald, "GeSi/Si Nanostructures," <u>Annual Review of Materials Science</u> , Vol. 25 (1995), pp. 417-454.							
CAT	C111	Frank, "Orientation-Dependent Dissolution of Germanium," <u>Journal of Applied Physics</u> , Vol. 31, No. 11 (November 1960), pp. 1996-1999.							

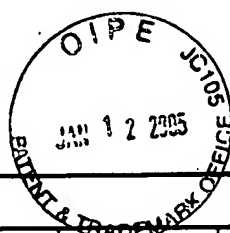
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FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT				ATTORNEY DOCKET NO.: ASC-025DVC1 APPLICANTS: Cheng <i>et al.</i> SERIAL NO.: 10/802,185 FILING DATE: March 17, 2004 GROUP: 2813					
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OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
CAT	C112	Fukatsu, "SiGe-based semiconductor-on-insulator substrate created by low-energy separation-by-implanted-oxygen," <u>Applied Physics Letters</u> , Vol. 72, No. 26 (June 29, 1998), pp. 3485-3487.							
UAT	C113	Ghandi <i>et al.</i> , "Chemical Etching of Germanium," <u>Journal of the Electrochemical Society</u> , Vol. 135, No. 8 (August 1988), pp.2053-2054.							
UAT	C114	Godbey <i>et al.</i> , "A Si _{0.7} Ge _{0.3} strained-layer etch stop for the generation of thin layer undoped silicon," <u>Applied Physics Letters</u> , Vol. 56, No. 4 (January 22, 1990), pp. 373-375.							
UAT	C115	Herzog <i>et al.</i> , "X-Ray Investigation of Boron- and Germanium-Doped Silicon Epitaxial Layers," <u>Journal of the Electrochemical Society</u> , Vol. 131, No. 12 (December 1984), pp.2969-2974.							
UAT	C116	Holmes, "The Orientation Dependence of Etching Effects on Germanium Crystals," <u>Acta Metallurgica</u> , Vol. 7, No. 4 (April 1959), pp. 283-290.							
CAT	C117	Huang <i>et al.</i> , "The Impact of Scaling Down to Deep Submicron on CMOS RF Circuits," <u>IEEE Journal of Solid State Circuits</u> , Vol. 33, No. 7 (July 1998), pp. 1023-1036							
CAT	C118	Hunt <i>et al.</i> , "Highly Selective Etch Stop by Stress Compensation for Thin-Film BESOI," <u>1990 IEEE/SOI Technology Conference</u> , (October 2-4, 1990), pp.145-146.							
UAT	C119	Jaccodine, "Use of Modified Free Energy Theorems to Predict Equilibrium Growing and Etching Shapes," <u>Journal of Applied Physics</u> , Vol. 33, No. 8 (August 1962), pp. 2643-2647.							
CAT	C120	Kern, "Chemical Etching of Silicon, Germanium, Gallium, Arsenide, and Gallium Phosphide," <u>RCA Review</u> , Vol. 39 (June 1978), pp. 278-308.							
UAT	C121	Lang <i>et al.</i> , "Bulk Micromachining of Ge for IR Gratings," <u>Journal of Micromechanics and Microengineering</u> , Vol. 6, No.1 (March 1996), pp. 46-48.							
UAT	C122	Leancu <i>et al.</i> , "Anisotropic Etching of Germanium," <u>Sensors and Actuators</u> , A46-47 (1995), pp. 35-37.							

EXAMINER

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7 APR 05

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EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)							
CAT	C123	LeGoues et al., "Relaxation of SiGe thin films grown on Si/SiO ₂ substrates," <u>Applied Physics Letters</u> , Vol. 75, No. 11 (June 1, 1994), pp. 7240-7246.						
CAT	C124	Lehmann <i>et al.</i> , "Implanted Carbon: An Effective Etch-Stop in Silicon," <u>Journal of the Electrochemical Society</u> , Vol. 138, No.5 (May 1991), pp. 3-4.						
CAT	C125	Narozny et al., "Si/SiGe Heterojunction Bipolar Transistor with Graded GAP SiGe Base Made by Molecular Beam Epitaxy," <u>IEEE IEDM</u> (1988), pp. 562-565.						
CAT	C126	Palik <i>et al.</i> , "Ellipsometric Study of the Etch-Stop Mechanism in Heavily Doped Silicon," <u>Journal of the Electrochemical Society</u> , Vol. 132, No. 1 (January 1985), pp. 135-141.						
CAT	C127	Palik <i>et al.</i> , "Study of Bias-Dependent Etching of Si in Aqueous KOH," <u>Journal of the Electrochemical Society</u> , Vol. 134, No. 2 (February 1987), pp. 404-409.						
CAT	C128	Palik <i>et al.</i> , "Study of the Etch-Stop Mechanism in Silicon," <u>Journal of the Electrochemical Society</u> , Vol. 129, No. 9 (September 1982), pp.2051-2059.						
CAT	C129	Petersen, "Silicon as a Mechanical Material," <u>Proceedings of the IEEE</u> , Vol. 70, No. 5 (May 1982), pp. 420-457.						
CAT	C130	Powell et al., "New approach to the growth of low dislocation relaxed SiGe material," <u>Applied Physics Letters</u> , Vol. 64, No. 14 (April 4, 1994), pp. 1865-1858.						
CAT	C131	Rai-Choudhury <i>et al.</i> , "Doping of Epitaxial Silicon," <u>Journal of Crystal Growth</u> , Vol. 7 (1970), pp. 361-367.						
CAT	C132	Raley <i>et al.</i> , "(100) Silicon Etch-Rate Dependence on Boron Concentration in Ethylenediamine-Pyrocatechol-Water Solutions," <u>Journal of the Electrochemical Society</u> , Vol. 131, No. 1 (January 1984), pp. 161-170.						
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EXAMINER	DATE CONSIDERED 7 APR 05
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EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
LAT	C134	Senna <i>et al.</i> , "Gallium Doping for Silicon Etch Stop in KOH," <u>Transducers '95/Euroensors IX</u> , the 8 th International Conference on Solid-State Sensors and Actuators and Euroensors IX, Stockholm, Sweden, June 25-29, 1995, pp. 194-195.							
LAT	C135	Shang <i>et al.</i> , "The Development of an Anisotropic Si Etch Process Selective to Ge _x Si _{1-x} Underlayers," <u>Journal of the Electrochemical Society</u> , Vol. 141, No. 2 (February 1994), pp. 507-510.							
LAT	C136	Soderbarg, "Fabrication of BESOI-Materials Using Implanted Nitrogen as an Effective Etch Stop Barrier," <u>1989 IEEE SOS/SOI Technology Conference</u> , (October 3-5, 1989), pp. 64.							
LAT	C137	Sundaram <i>et al.</i> , "Electrochemical etching of Silicon by Hydrazine," <u>Journal of the Electrochemical Society</u> , Vol. 140, No. 6 (June 1993), pp. 1592-1597.							
LAT	C138	Sze, "Physics of Semiconductor Devices," (1991).							
LAT	C139	Takagi <i>et al.</i> , "On the Universality of Inversion Layer Mobility in Si MOSFET's: Part I-Effects of Substrate Impurity Concentration," <u>IEEE Transactions on Electron Devices</u> , Vol. 41, No. 12 (December 1994), pp. 2357-2362.							
LAT	C140	Ting <i>et al.</i> , "Monolithic Integration of III-V Materials and Devices on Silicon," Part of the SPIE Conference on Silicon-Based Optoelectronics, San Jose, CA, (January 1999), pp. 19-28.							
LAT	C141	Vol'fson <i>et al.</i> , "Fundamental Absorption Edge of Silicon Heavily Doped with Donor or Acceptor Impurities," <u>Soviet Physics Semiconductors</u> , Vol. 1, No. 3 (September 1967), pp. 327-332.							
LAT	C142	Wu, "Novel Etch-Stop Materials for Silicon Micromachining," Thesis Submitted to the Massachusetts Institute of Technology Department of Materials Science and Engineering on May 9, 1997, pp. 1-62.							
LAT	C143	Yi <i>et al.</i> , "Si _{1-x} Ge _x /Si Multiple Quantum Well Wires Fabricated Using Selective Etching," <u>Materials Research Society Symposium Proceedings</u> , Vol. 379 (1995), pp. 91-96.							

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